**Supporting Information**

**Force and impulse multi-sensor based on flexible gate dielectric field effect transistor**

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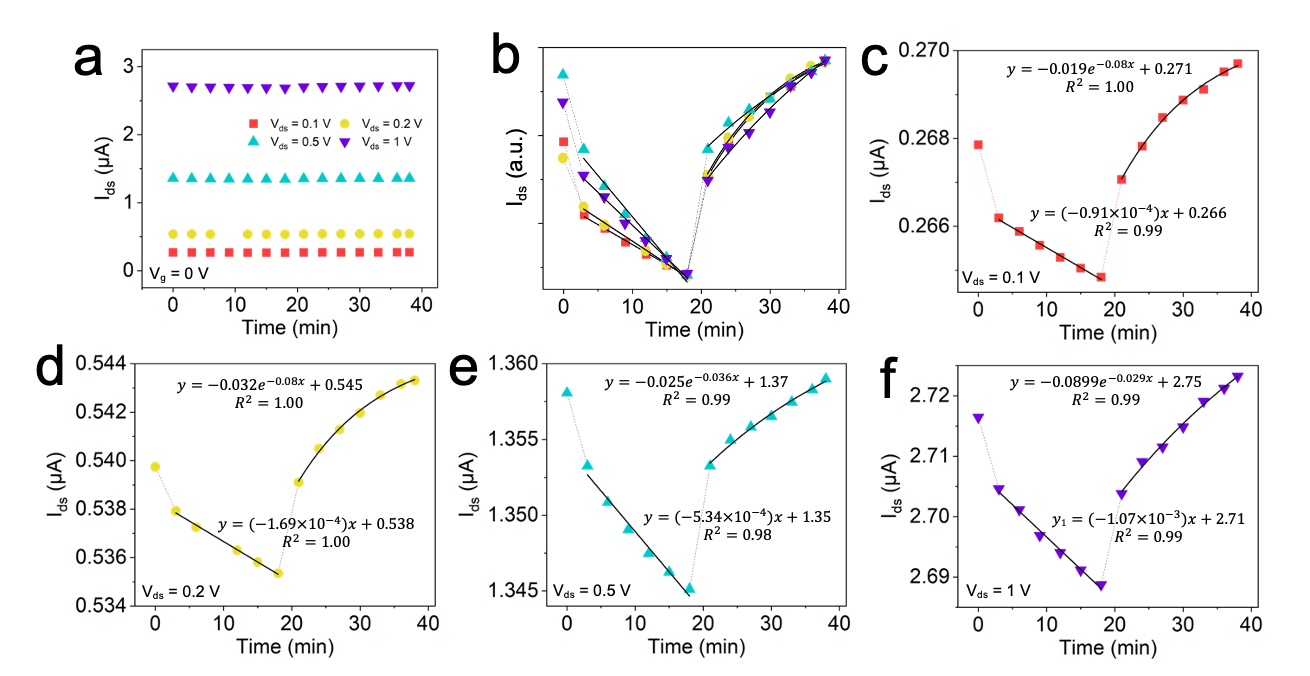


Fig. S1. (a) Zero-*V*g field-effect responses under different *V*ds values and (b) its normalization curves. The zero-*V*g field-effect responses under *V*ds values of (c) 0.1 V, (d) 0.2 V, (e) 0.5 V, and (f) 1 V.

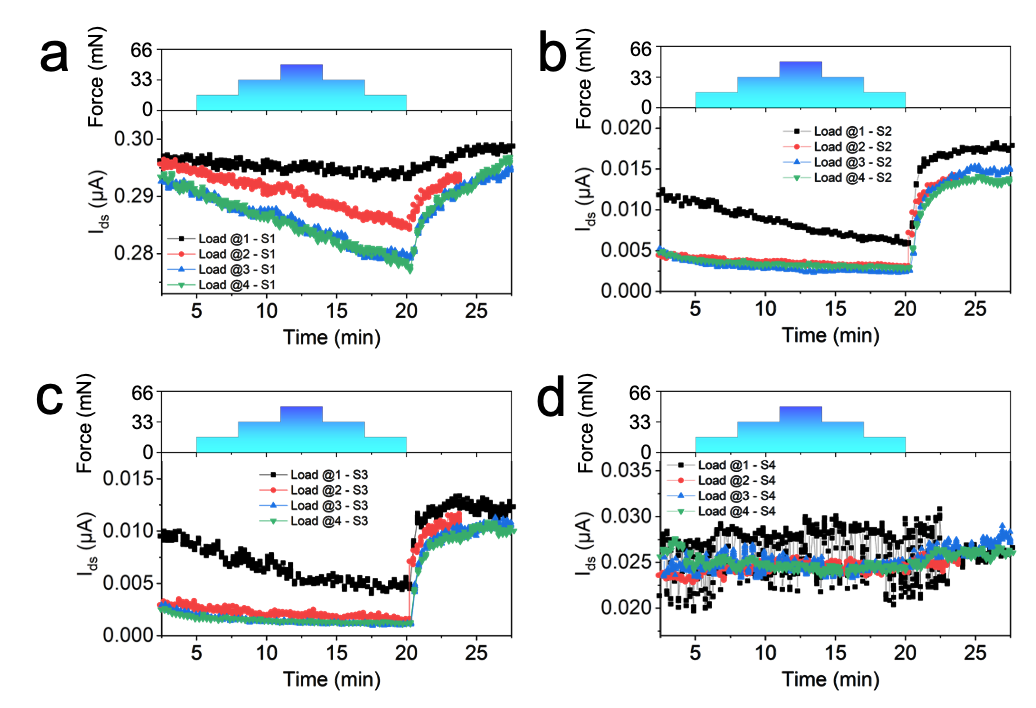


Fig. S2. Real-time *I*ds responses of the sensor array with different applied forces.